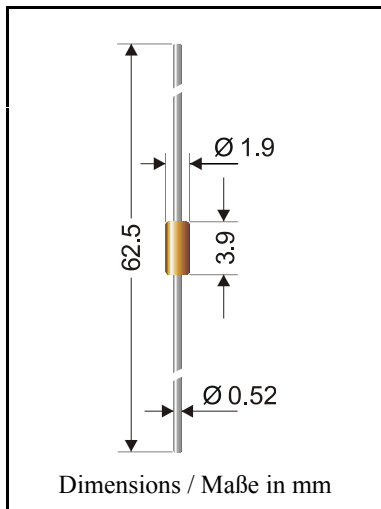


**Bidirectional Si-Trigger-Diodes (DIAC)**

**Bidirektionale Si-Trigger-Dioden (DIAC)**



|  |                               |
|--|-------------------------------|
| Breakover voltage<br>Durchbruchsspannung   | 28 ... 45 V                   |
| Peak pulse current<br>Max. Triggerimpuls   | ± 2 A                         |
| Glass case<br>Glasgehäuse  | DO-35<br>SOD-27               |
| Weight approx.<br>Gewicht ca.  | 0.13 g                        |
| Standard packaging taped in ammo pack<br>Standard Lieferform gegurtet in Ammo-Pack | see page 16<br>siehe Seite 16 |

**Maximum ratings**

**Grenzwerte**

|   |                                  |           |                      |
|---|----------------------------------|-----------|----------------------|
| Power dissipation – Verlustleistung   | $T_A = 50\text{ °C}$             | $P_{tot}$ | 150 mW <sup>1)</sup> |
| Peak pulse current (120 pulse repetition rate)<br>Max. Triggerstrom (120 Impulse) | $t_p \leq 10\text{ }\mu\text{s}$ | $I_{PM}$  | ± 2 A <sup>1)</sup>  |
| Operating junction temperature – Sperrschichttemperatur                           |                                  | $T_j$     | – 40...+100°C        |
| Storage temperature – Lagerungstemperatur   |                                  | $T_s$     | – 40...+150°C        |

**Characteristics**

**Kennwerte**

|   |                     |                           |                      |                            |
|---|---------------------|---------------------------|----------------------|----------------------------|
| Breakover voltage<br>Durchbruchsspannung  | $dV/dt = 10V/\mu s$ | DB 3<br>DB 4              | $V_{BO}$<br>$V_{BO}$ | 28 ... 36 V<br>35 ... 45 V |
| Breakover current – Durchbruchstrom   |                     | $V = 98\% V_{BO}$         | $I_{BO}$             | < 200 $\mu A$              |
| Asymmetry of breakover voltage<br>Unsymmetrie der Durchbruchspannung                        |                     | $ V_{(BO)F} - V_{(BO)R} $ | $\Delta V_{BO}$      | < 3.8 V                    |
| Foldback voltage – Spannungs-Rücksprung<br>$\Delta I = I_{BO}$ to/auf $I_F = 10\text{ mA}$  | $dV/dt = 10V/\mu s$ |                           | $\Delta V_{F/R}$     | > 5 V                      |
| Thermal resistance junction to ambient air<br>Wärmewiderstand Sperrschicht – umgebende Luft |                     |                           | $R_{thA}$            | < 60 K/W <sup>1)</sup>     |

<sup>1)</sup> Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

Gültig, wenn die Anschlußdrähte in 10 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

